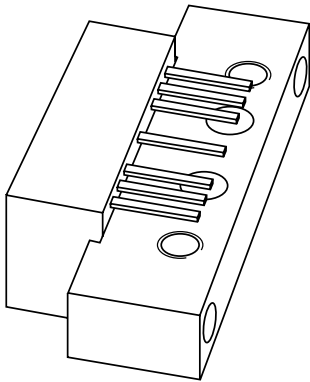


DATA SHEET



BGD816L

**860 MHz, 21.5 dB gain power
doubler amplifier**

Product specification
Supersedes data of 2001 May 18

2001 Nov 15

860 MHz, 21.5 dB gain power doubler amplifier

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FEATURES

- Excellent linearity
- Extremely low noise
- Excellent return loss properties
- Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability.

APPLICATIONS

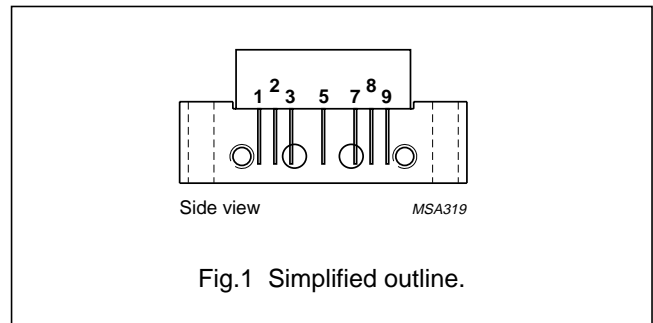
- CATV systems operating in the 40 to 870 MHz frequency range.

DESCRIPTION

Hybrid amplifier module in a SOT115J package operating with a voltage supply of 24 V (DC).

PINNING - SOT115J

PIN	DESCRIPTION
1	input
2, 3	common
5	+V _B
7, 8	common
9	output



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 45 MHz	21.2	21.8	dB
		f = 870 MHz	22	23	dB
I _{tot}	total current consumption (DC)	V _B = 24 V	345	375	mA

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _B	supply voltage	–	30	V
V _i	RF input voltage	–	70	dBmV
T _{stg}	storage temperature	–40	+100	°C
T _{mb}	operating mounting base temperature	–20	+100	°C

860 MHz, 21.5 dB gain power doubler amplifier

BGD816L

CHARACTERISTICSBandwidth 40 to 870 MHz; $V_B = 24$ V; $T_{mb} = 35$ °C; $Z_S = Z_L = 75$ Ω

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G _p	power gain	f = 45 MHz	21.2	–	21.8	dB
		f = 870 MHz	22	–	23	dB
SL	slope straight line	f = 45 to 870 MHz; note 1	0.5	1	1.5	dB
FL	flatness straight line	f = 45 to 100 MHz	–	–	±0.25	dB
		f = 100 to 800 MHz	–	–	±0.5	dB
		f = 800 to 870 MHz	–0.4	–	0.1	dB
S ₁₁	input return losses	f = 45 to 80 MHz	22	–	–	dB
		f = 80 to 160 MHz	21	–	–	dB
		f = 160 to 320 MHz	19	–	–	dB
		f = 320 to 550 MHz	18	–	–	dB
		f = 550 to 650 MHz	17	–	–	dB
		f = 650 to 750 MHz	16	–	–	dB
		f = 750 to 870 MHz	15	–	–	dB
		f = 870 to 914 MHz	12	–	–	dB
S ₂₂	output return losses	f = 45 to 80 MHz	25	–	–	dB
		f = 80 to 160 MHz	23	–	–	dB
		f = 160 to 320 MHz	18	–	–	dB
		f = 320 to 550 MHz	17	–	–	dB
		f = 550 to 650 MHz	16	–	–	dB
		f = 650 to 750 MHz	15	–	–	dB
		f = 750 to 870 MHz	15	–	–	dB
		f = 870 to 914 MHz	12	–	–	dB
S ₂₁	phase response	f = 50 MHz	–45	–	+45	deg
CTB	composite triple beat	79 chs flat; V _o = 44 dBmV; f _m = 547.25 MHz	–	–	–66	dB
		112 chs flat; V _o = 44 dBmV; f _m = 745.25 MHz	–	–	–59.5	dB
		132 chs flat; V _o = 44 dBmV; f _m = 859.25 MHz	–	–	–55	dB
		112 chs; f _m = 547.25 MHz; V _o = 48.2 dBmV at 745 MHz; note 2	–	–	–59	dB
		79 chs; f _m = 331.25 MHz; V _o = 45.3 dBmV at 547 MHz; note 3	–	–	–68.5	dB
X _{mod}	cross modulation	79 chs flat; V _o = 44 dBmV; f _m = 55.25 MHz	–	–	–64	dB
		112 chs flat; V _o = 44 dBmV; f _m = 55.25 MHz	–	–	–61	dB
		132 chs flat; V _o = 44 dBmV; f _m = 55.25 MHz	–	–	–58	dB
		112 chs; f _m = 745.25 MHz; V _o = 48.2 dBmV at 745 MHz; note 2	–	–	–60	dB
		79 chs; f _m = 445.25 MHz; V _o = 45.3 dBmV at 547 MHz; note 3	–	–	–66	dB

860 MHz, 21.5 dB gain power doubler amplifier

BGD816L

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
CSO	composite second order distortion	79 chs flat; $V_o = 44$ dBmV; $f_m = 548.5$ MHz	–	–	–66	dB
		112 chs flat; $V_o = 44$ dBmV; $f_m = 746.5$ MHz	–	–	–58	dB
		132 chs flat; $V_o = 44$ dBmV; $f_m = 860.5$ MHz	–	–	–56	dB
		112 chs; $f_m = 210.0$ MHz; $V_o = 48.2$ dBmV at 745 MHz; note 2	–	–	–57	dB
		79 chs; $f_m = 210.0$ MHz; $V_o = 45.3$ dBmV at 547 MHz; note 3	–	–	–64	dB
d_2	second order distortion	note 4	–	–	–70	dB
V_o	output voltage	$d_{im} = -60$ dB; note 5	62	–	–	dBmV
		CTB compression = 1 dB; 132 chs flat; $f = 859.25$ MHz	48	–	–	dBmV
		CSO compression = 1 dB; 132 chs flat; $f = 860.5$ MHz	49	–	–	dBmV
NF	noise figure	$f = 50$ MHz	–	–	5.5	dB
		$f = 550$ MHz	–	–	5.5	dB
		$f = 750$ MHz	–	–	6.5	dB
		$f = 870$ MHz	–	–	7.5	dB
I_{tot}	total current consumption (DC)	note 6	345	360	375	mA

Notes

- Slope straight line is defined as gain at 870 MHz against gain at 45 MHz.
- Tilt = 10.2 dB (55 to 745 MHz).
- Tilt = 7.3 dB (55 to 547 MHz).
- $f_p = 55.25$ MHz; $V_p = 44$ dBmV;
 $f_q = 805.25$ MHz; $V_q = 44$ dBmV;
measured at $f_p + f_q = 860.5$ MHz.
- Measured according to DIN45004B:
 $f_p = 851.25$ MHz; $V_p = V_o$;
 $f_q = 858.25$ MHz; $V_q = V_o - 6$ dB;
 $f_r = 860.25$ MHz; $V_r = V_o - 6$ dB;
measured at $f_p + f_q - f_r = 849.25$ MHz.
- The module normally operates at $V_B = 24$ V, but is able to withstand supply transients up to 35 V.

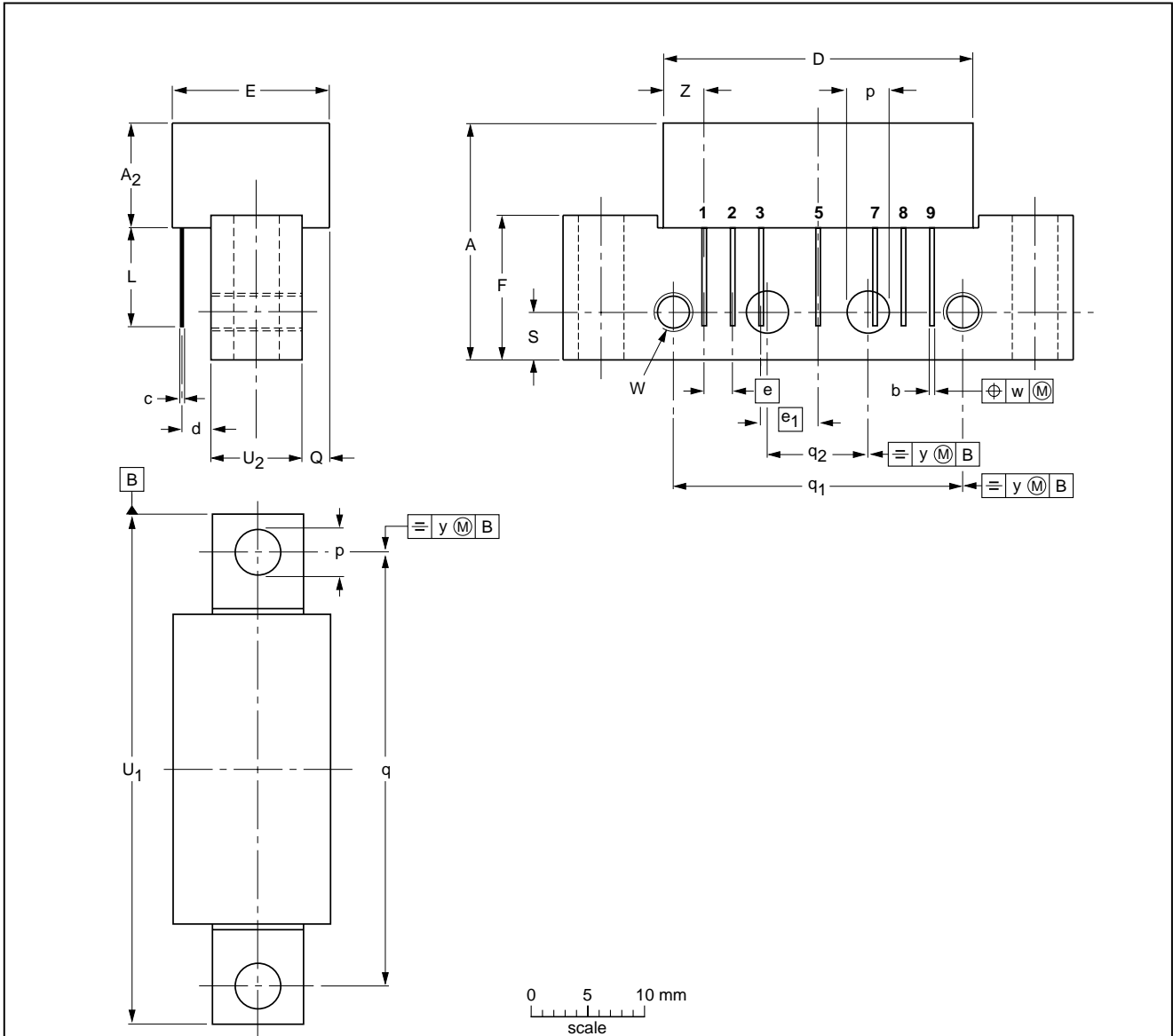
860 MHz, 21.5 dB gain power doubler amplifier

BGD816L

PACKAGE OUTLINE

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads

SOT115J



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₂ max.	b	c	D max.	d max.	E max.	e	e ₁	F	L min.	p	Q max.	q	q ₁	q ₂	S	U ₁ max.	U ₂	W	w	y	Z max.
mm	20.8	9.1	0.51 0.38	0.25	27.2	2.54	13.75	2.54	5.08	12.7	8.8	4.15 3.85	2.4	38.1	25.4	10.2	4.2	44.75	8	6-32 UNC	0.25	0.1	3.8

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT115J						99-02-06

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BGD816L

DATA SHEET STATUS

DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITIONS
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This product is supplied in anti-static packing to prevent damage caused by electrostatic discharge during transport and handling. For further information, refer to Philips specs.: SNW-EQ-608, SNW-FQ-302A and SNW-FQ-302B.

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BGD816L

NOTES

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